



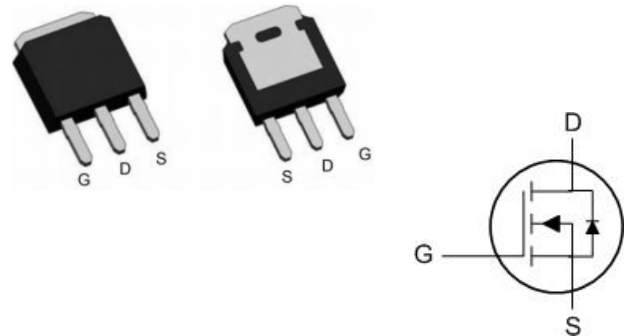
- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

BVDSS	RDSON	ID
30V	3.5mΩ	100A

Description

The XXW100N03Z is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The XXW100N03Z meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO251 Pin Configuration

Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^{\circ}\text{C}$	100	A
		$T_C = 100^{\circ}\text{C}$	65	A
I_{DM}	Pulsed Drain Current ^{note1}		400	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		95	mJ
P_D	Power Dissipation	$T_C = 25^{\circ}\text{C}$	80	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.9	$^{\circ}\text{C/W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	$^{\circ}\text{C}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} = 0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =30A	-	3.5	4.7	mΩ
		V _{GS} =4.5V, I _D =20A	-	5.5	10	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f = 1.0MHz	-	2100	-	pF
C _{oss}	Output Capacitance		-	326	-	pF
C _{rss}	Reverse Transfer Capacitance		-	282	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =30A, V _{GS} =10V	-	45	-	nC
Q _{gs}	Gate-Source Charge		-	3	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	15	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =30A, R _{GEN} =3Ω, V _{GS} =10V	-	21	-	ns
t _r	Turn-on Rise Time		-	32	-	ns
t _{d(off)}	Turn-off Delay Time		-	59	-	ns
t _f	Turn-off Fall Time		-	34	-	ns
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=100A/μs	-	15	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	4	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^{\circ}\text{C}$, $V_G=10V$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{AS}=18.4A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Figure1: Output Characteristics

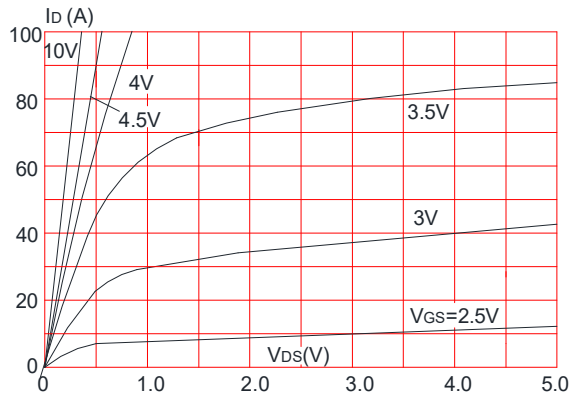


Figure 2: Typical Transfer Characteristics

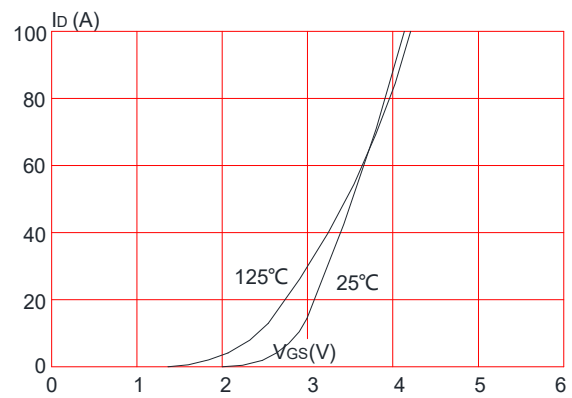


Figure 3: On-resistance vs. Drain Current

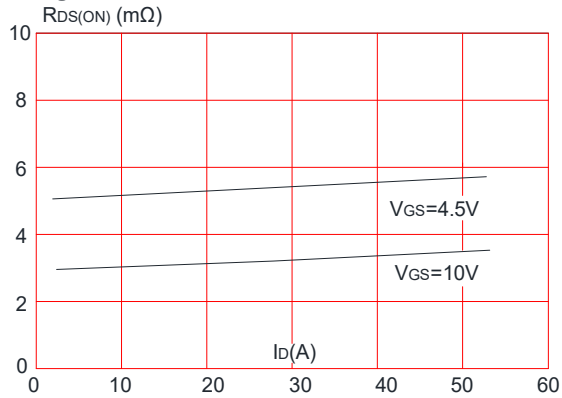


Figure 4: Body Diode Characteristics

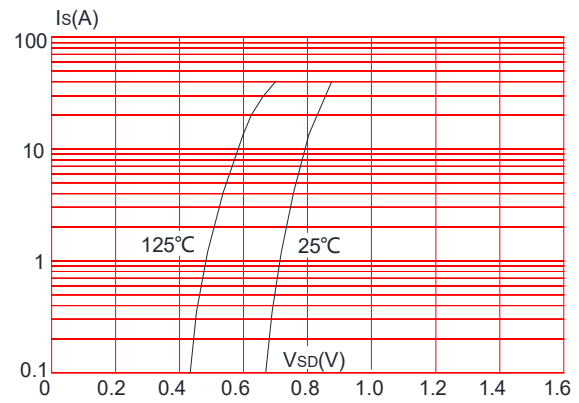


Figure 5: Gate Charge Characteristics

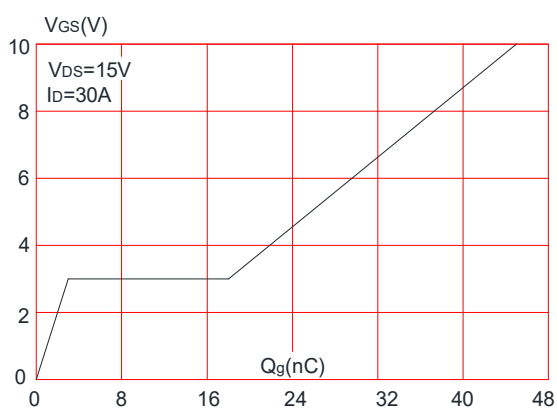


Figure 6: Capacitance Characteristics

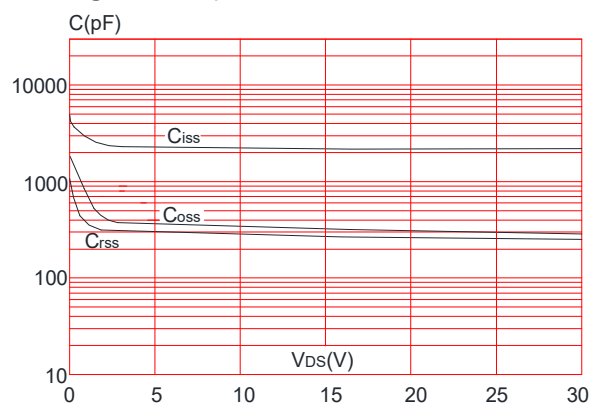


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

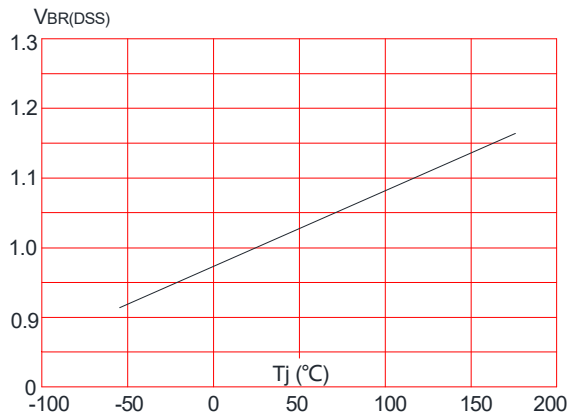


Figure 8: Normalized on Resistance vs. Junction Temperature

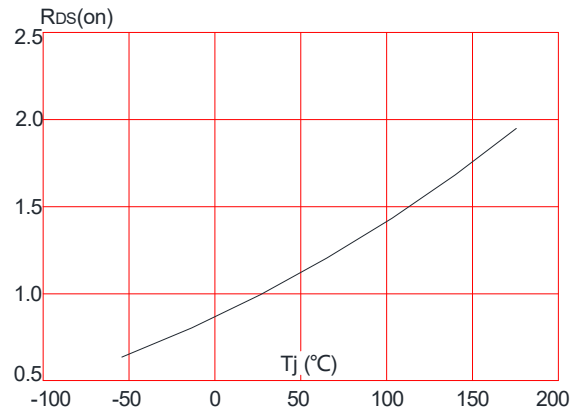


Figure 9: Maximum Safe Operating Area

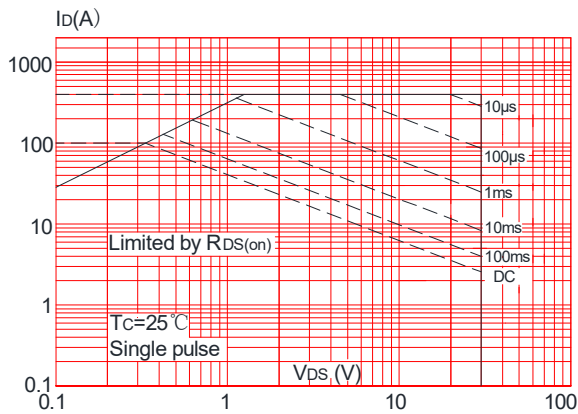


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

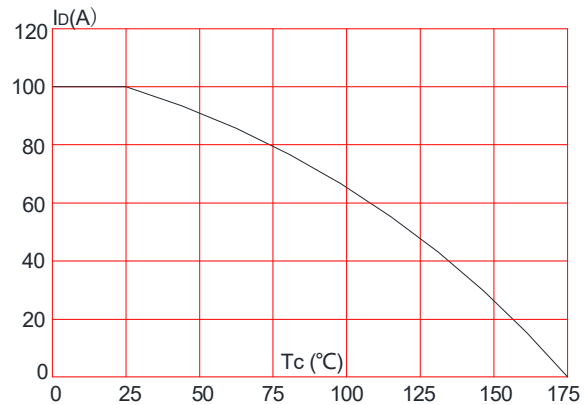
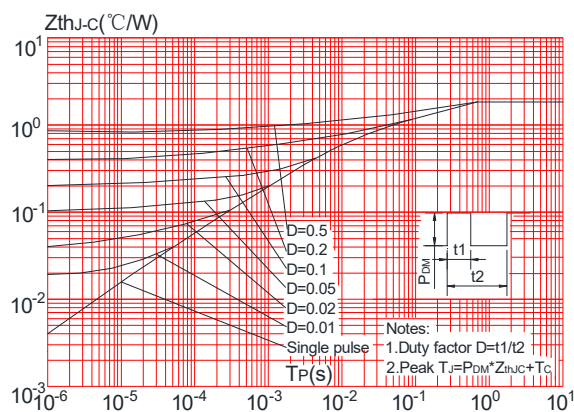


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

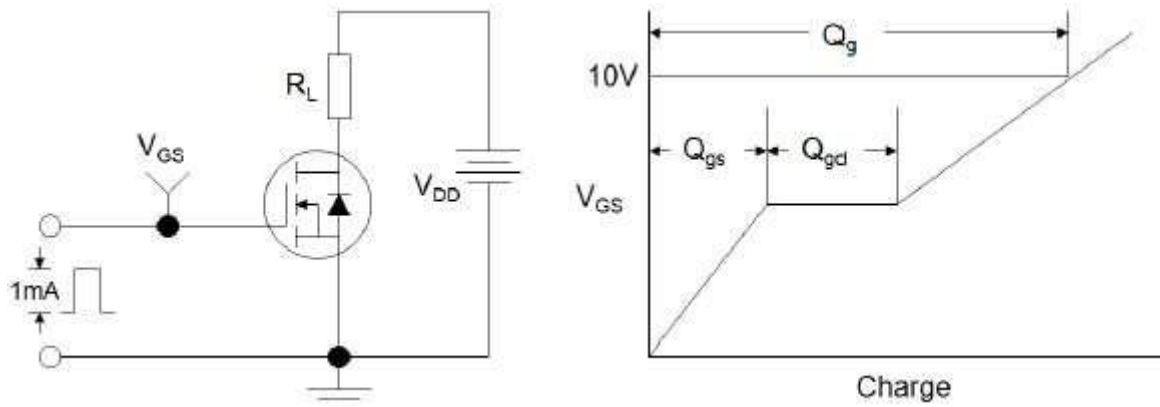


Figure1:Gate Charge Test Circuit & Waveform

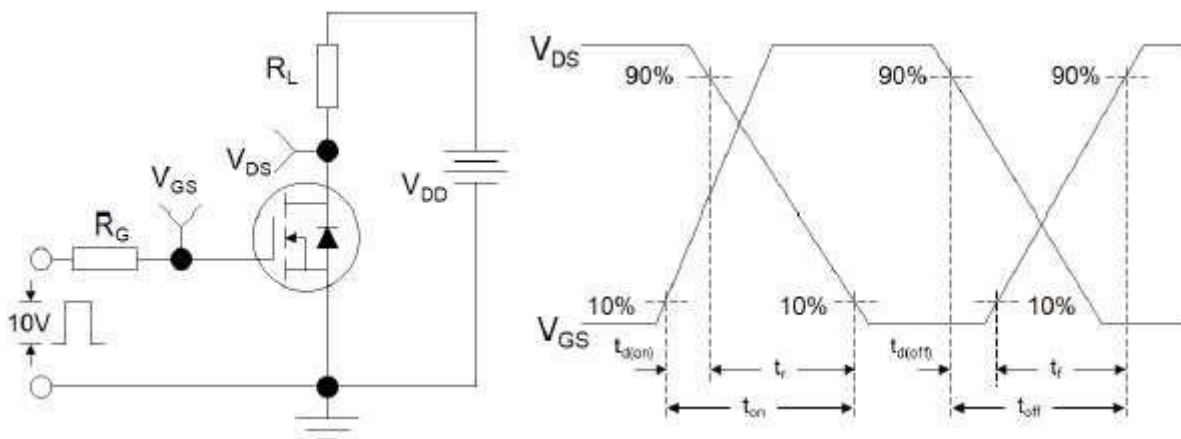


Figure 2: Resistive Switching Test Circuit & Waveforms

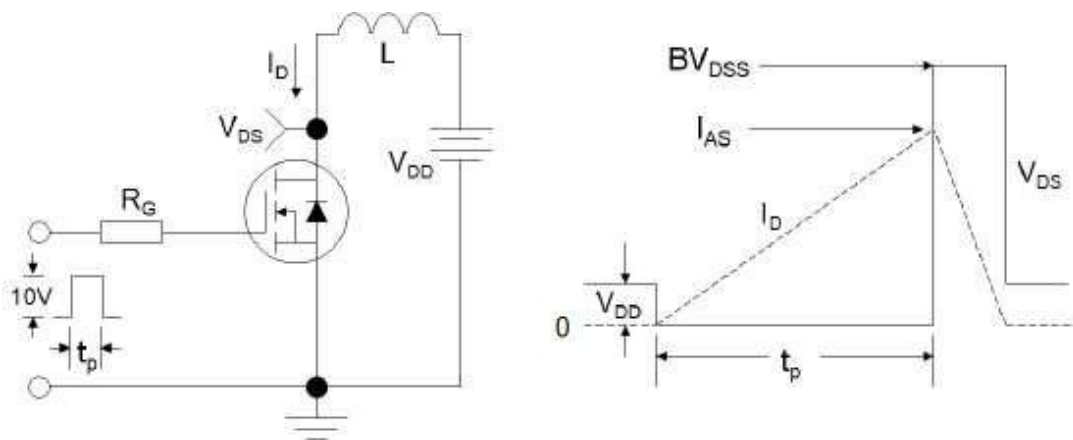


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data TO 251

